

# LML6402G-VB Datasheet

# P-Channel 20-V (D-S) MOSFET

MOSFET PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
	0.060 at V <sub>GS</sub> = - 10 V	- 4.0			
- 20	0.065 at V <sub>GS</sub> = - 4.5 V	- 3.5	10 nC		
	0.080 at V <sub>GS</sub> = - 2.5 V	- 2.0			

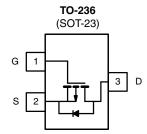
## **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

- · Load Switch
- PA Switch
- DC/DC Converters



Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	$V_{DS}$	- 20	V		
Gate-Source Voltage	V <sub>GS</sub>	± 12			
	T <sub>C</sub> = 25 °C		- 4 <sup>e</sup>	A	
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	$T_C = 70  ^{\circ}C$	I <sub>D</sub>	-3.2		
Continuous Brain Garrent (1) = 100 0)	T <sub>A</sub> = 25 °C	טי	- 3 .5 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		- 2 .5 <sup>b, c</sup>		
Pulsed Drain Current	I <sub>DM</sub>	- 10	7		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	Is	- 2.1		
Continuous Source-Diam Diode Current	T <sub>A</sub> = 25 °C	'S	- 1.0 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		2.5		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	1.6	w	
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C		1.25 <sup>b, c</sup>	. vv	
	T <sub>A</sub> = 70 °C		0.8 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>b, d</sup>	≤ 5 s	R <sub>thJA</sub>	75	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	40	50	7 5/**		

#### Notes:

- a. Based on T<sub>C</sub> = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 166 °C/W.
- e. Package limited.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 13.4		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μA		2.9		- mv/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 0.5		- 1.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zava Cata Valtaga Dvain Current		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 10			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3 A		0.060			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2.5 A		0.065		Ω	
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 2 A		0.080			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 3 A		15		S	
Dynamic <sup>b</sup>					l		
Input Capacitance	C <sub>iss</sub>			835		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		180			
Reverse Transfer Capacitance	C <sub>rss</sub>			155			
T. 10 . 0		V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.1 A		10			
Total Gate Charge		50 GO 5		6.4		nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -2.5 \text{ V}, I_{D} = -3.1 \text{ A}$		1.7			
Gate-Drain Charge	$Q_{gd}$	30 3		3.4			
Gate Resistance	$R_{g}$	f = 1 MHz	0.9	4.4	8.8	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			22	33		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V, R}_{L} = 2.4 \Omega$		20	30		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D = -3.1 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		28	42	ns ns	
Fall Time	t <sub>f</sub>			9	18		
<b>Drain-Source Body Diode Characteristic</b>	cs				L	<u>.</u> L	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 2.1	_	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 1 0	A	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 3.1 A		- 0.8	- 1.2	٧	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	-		23	35	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	<b>-</b>		12	20	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = -3.1 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 ^{\circ}\text{C}$		15			
Reverse Recovery Rise Time				8		ns	

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

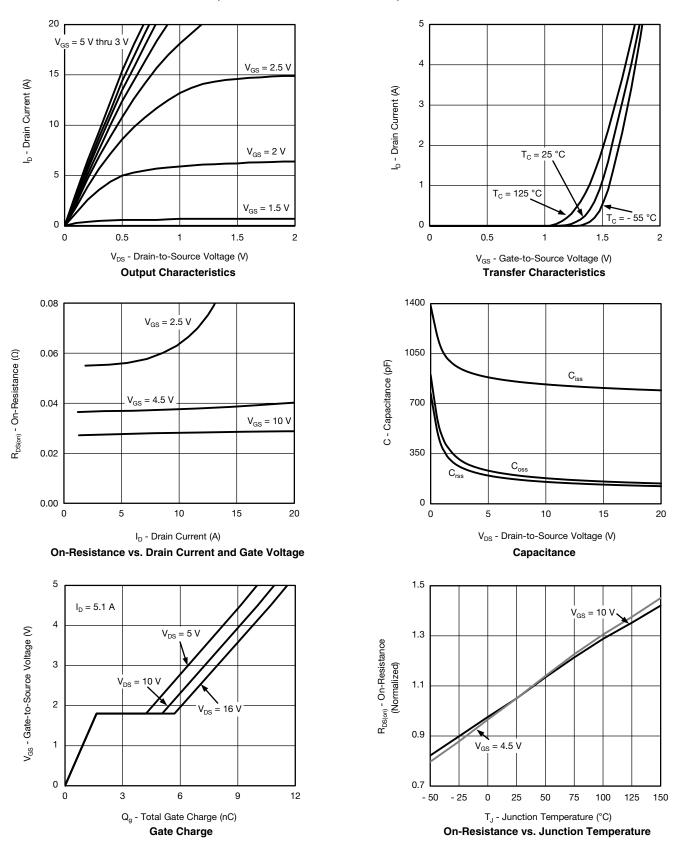
a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.



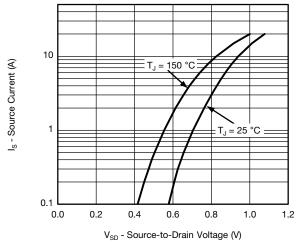
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## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

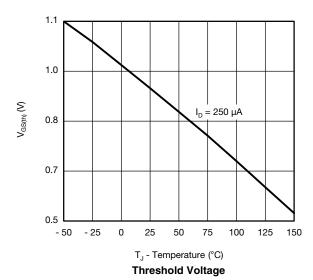


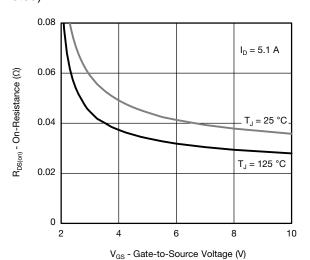


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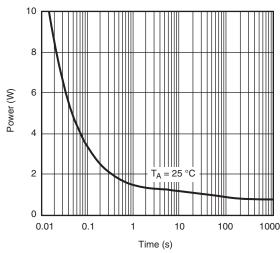


#### Source-Drain Diode Forward Voltage

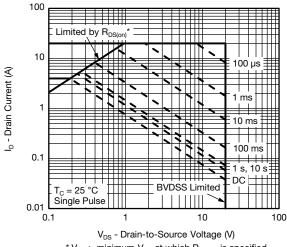




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power

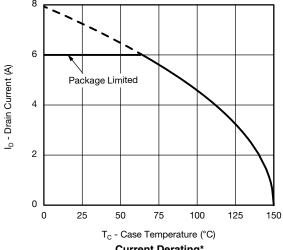


\*  $V_{\text{GS}} > \text{minimum } V_{\text{GS}}$  at which  $R_{\text{DS(on)}}$  is specified

Safe Operating Area

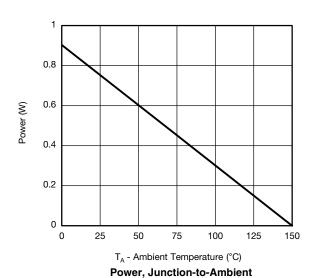


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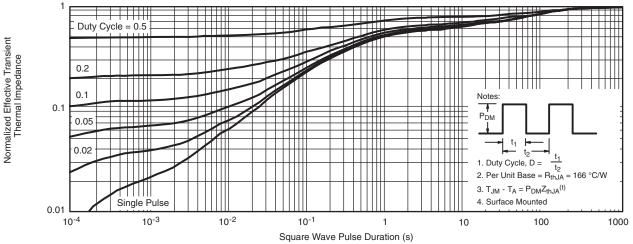




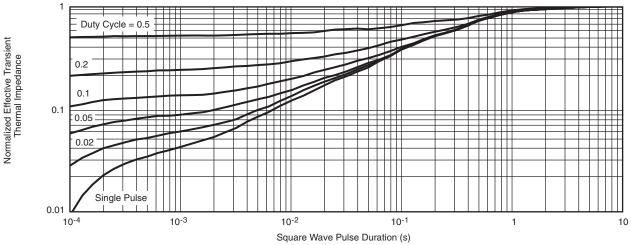
 $<sup>^*</sup>$  The power dissipation  $P_D$  is based on  $T_{J(max)}$  = 150  $^{\circ}$ C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



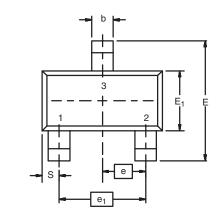




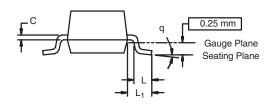
Normalized Thermal Transient Impedance, Junction-to-Foot



# SOT-23 (TO-236): 3-LEAD





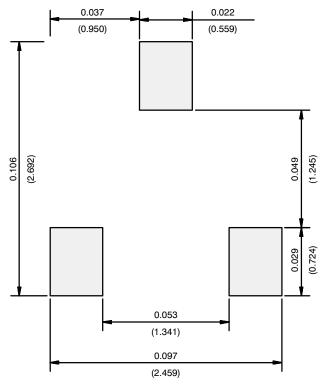


Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479



## **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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